**Product data sheet** 

# 1. General description

Planar passivated sensitive gate four quadrant triac in a TO92 plastic package. This sensitive gate "series E" triac is intended for interfacing with low power drivers including microcontrollers.

### 2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing with low power gate drivers and microcontrollers
- High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Triggering in all four quadrants

## 3. Applications

- Air conditioner indoor fan control
- General purpose low power motor control
- · General purpose switching and phase control

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Absolute	Absolute maximum rating								
$V_{DRM}$	repetitive peak off-state voltage			-	-	600	V		
I <sub>T(RMS)</sub>	RMS on-state current full sine wave; T <sub>lead</sub> ≤ 51.2 °C; Fig. 1; Fig. 2; Fig. 3			-	-	1	А		
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5		-	-	12.5	А		
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$		-	-	13.7	А		
T <sub>j</sub>	junction temperature			-	-	125	°C		
Static ch	aracteristics								
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$		-	-	10	mA		
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;} $ $T_j = 25 \text{ °C; } Fig. 7$		-	-	10	mA		
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	-	10	mA		
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	-	10	mA		

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1.3	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; $R_{GT1(ext)}$ = 1 k $\Omega$	50	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; dI_{com}/dt = 0.5 \text{ A/ms};$ $I_T = 1 \text{ A}; gate open circuit}$	5	-	-	V/µs

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		
2	G	gate	1 1,1,1,1	T2—T1
3	T1	main terminal 1		sym051

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT131-600E	TO92	BT131-600E,412	Bulk	1000	SOT54	14-Nov-2013
BT131-600E	TO92	BT131-600EQP	Reel	2000	SOT54	14-Nov-2013

# 7. Marking

## Table 4. Marking codes

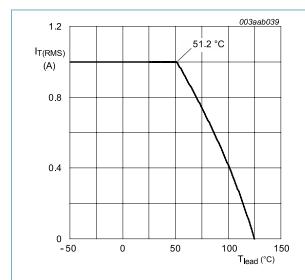
Type number	Marking codes
BT131-600E	131-6E

# 8. Limiting values

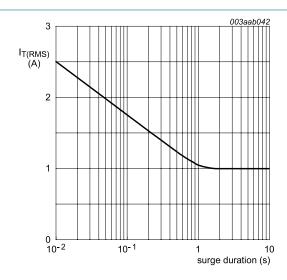
#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 51.2 °C; Fig 1; Fig 2; Fig 3	-	1	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig 4; Fig 5	-	12.5	А
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	13.7	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>P</sub> = 10 ms; SIN	-	0.78	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state	I <sub>G</sub> = 20 mA	-	50	A/µs
	current		-	50	A/µs
			-	10	A/µs
			-	50	A/µs
$I_{GM}$	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C

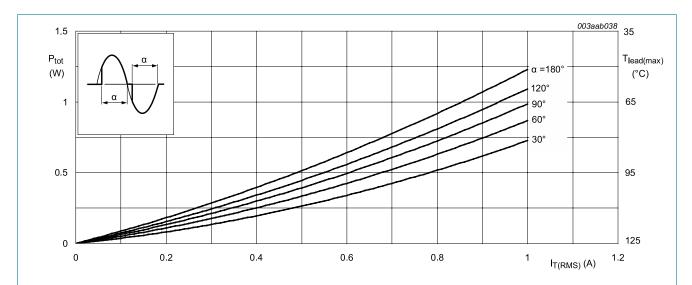


T<sub>lead</sub> = 51.2 °C
Fig. 1. RMS on-state current as a function of lead temperature; maximum values



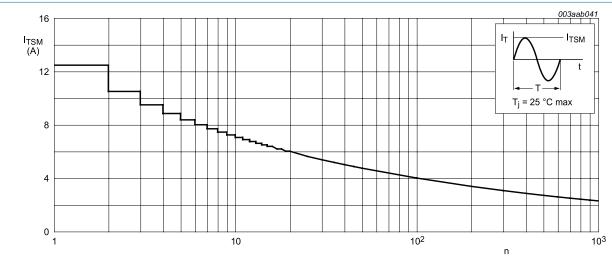
f = 50 Hz;  $T_{lead}$  = 51.2 °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values



 $\alpha$  = conduction angle

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum value

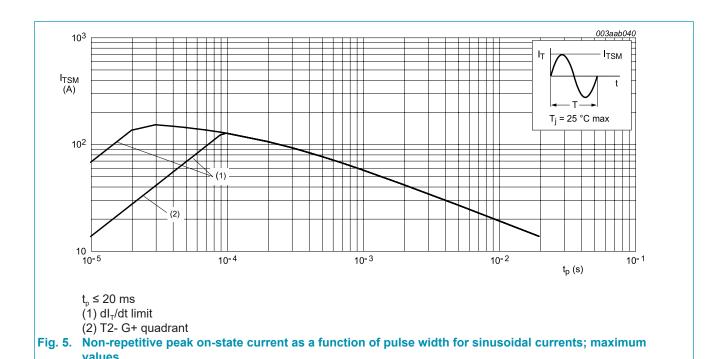


f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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**4Q Triac** 



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance	full cycle; Fig 6	-	-	60	K/W
from junction to lead		half cycle; <u>Fig 6</u>	-	-	80	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

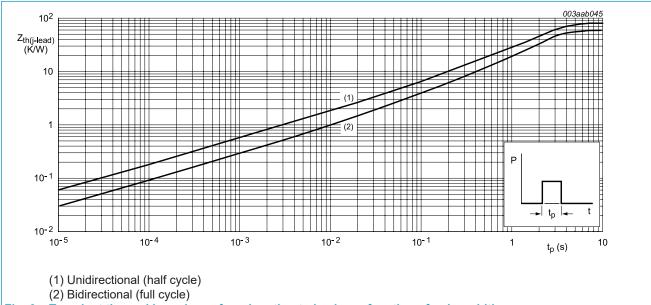
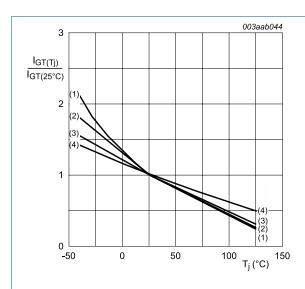


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;} $ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
I <sub>L</sub> la	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	15	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1.3	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C	0.2	0.3	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics		·	'		
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; $R_{GT1(ext)}$ = 1 k $\Omega$	50	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; dI_{com}/dt = 0.5 \text{ A/}$ ms; $I_T = 1 \text{ A};$ gate open circuit	5	-	-	V/µs
<b>t</b> <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 1.5 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

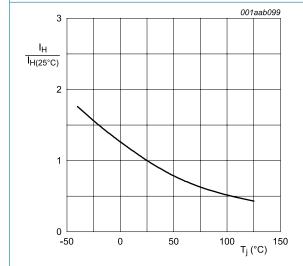


Fig. 9. Normalized holding current as a function of junction temperature

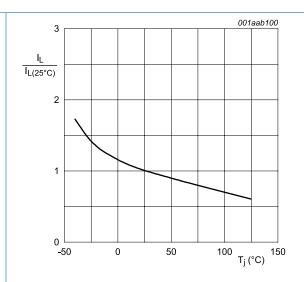
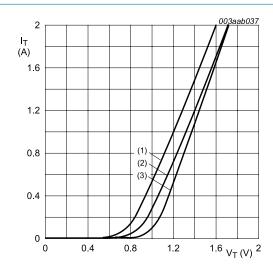


Fig. 8. Normalized latching current as a function of junction temperature



- $V_o = 0.92 \text{ V}; R_s = 0.4 \Omega$
- (1) T<sub>j</sub> = 125 °C; typical values (2) T<sub>j</sub> = 125 °C; maximum values
- (3)  $T_i = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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**4Q Triac** 

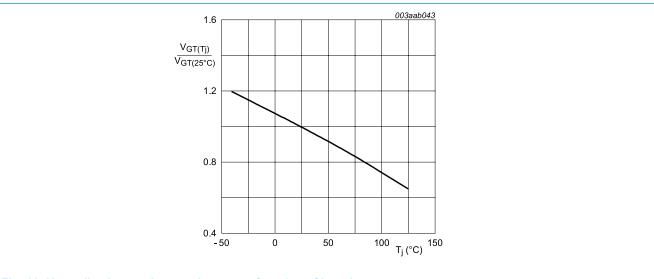
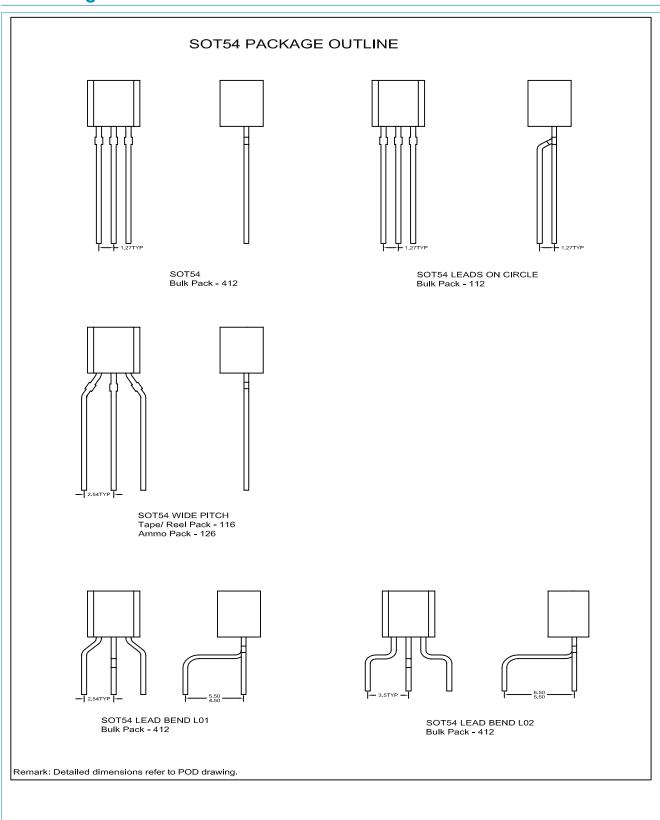
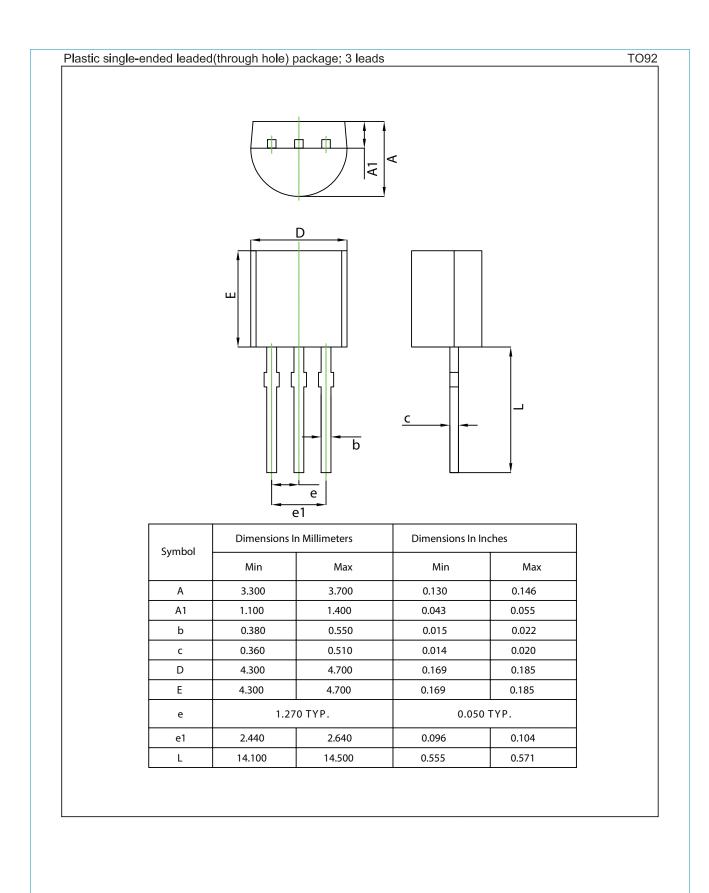


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

# 11. Package outline





**40 Triac** 

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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For more information, please visit: http://www.ween-semi.com
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Date of release: 19 October 2021

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